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NEWS 1 Web Page URLs for STN Seminar Schedule - N. America
NEWS 2 Jan 15 BLAST(R) searching in REGISTRY available in STN on the Web
NEWS 3 Jan 29 FSTA has been reloaded and moves to weekly updates
NEWS 4 Feb 01 CHEMLIT now produced by FIZ Karlsruhe and has a new update frequency
NEWS 5 Feb 19 Access via Tymnet and SprintNet Elimination Effective 3/31/02
NEWS 6 Mar 04 Gene Names now available in BIOSIS
NEWS 7 Mar 11 TOXLIT no longer available
NEWS 8 Mar 11 TROTHERMO no longer available
NEWS 9 Mar 25 US Provisional Priorities searched with P in CA/CAplus and USPATFULL
NEWS 10 Mar 25 LIPINSKI/CALC added for property searching in REGISTRY
NEWS 11 Apr 01 PAPERCHEM no longer available in STN. Use PAPERCHEM2 instead.
NEWS 12 Apr 08 "Ask CAS" for self-help around the clock
NEWS 13 Apr 15 BEILSTEIN: Reload and Implementation of a New Subject Area
NEWS 14 Apr 15 ZDB will be removed from STN
NEWS 15 Apr 16 US Patent Applications available in IFICDB, IFIPAT, and IFIUDB
NEWS 16 Apr 16 Records from 18 pcs available in CAPLUS, HCAPLUS, and ZCAPLUS
NEWS 17 Apr 17 BIOSIS Gene Names now available in TOXCENTER
NEWS 18 Apr 22 Federal Research in Progress (FEDRIP) now available
NEWS 19 May 01 PCTFULL to be reloaded. File temporarily unavailable.
NEWS 20 Jun 03 New e-mail delivery for search results now available

NEWS EXPRESS February 1 CURRENT WINDOWS VERSION IS V6.0a, CURRENT MACINTOSH VERSION IS V6.0a(ENG) AND V6.0Ja(JP), AND CURRENT DISCOVER FILE IS DATED 01 FEBRUARY 2002.
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FILE 'HOME' ENTERED AT 08:33:04 ON 04 JUN 2002

=> file registry
COST IN U.S. DOLLARS SINCE FILE ENTRY 0.21 TOTAL SESSION 0.21

FULL ESTIMATED COST 0.21 0.21

FILE 'REGISTRY' ENTERED AT 08:33:41 ON 04 JUN 2002

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STRUCTURE FILE UPDATES: 2 JUN 2000 HIGHEST RN 347787-52-0
DICTIONARY FILE UPDATES: 2 JUN 2000 HIGHEST RN 347787-52-0

TSCA INFORMATION NOW CURRENT THROUGH January 9, 2000

Please note that search-term pricing does apply when conducting SmartSELECT searches.

Crossover limits have been increased. See HELP CROSSOVER for details.

Calculated physical property data is now available. See HELP PROPERTIES for more information. See STNote 7, Searching Properties in the CAS Registry File, for complete details:
http://www.cas.org/ONLINE/STN/STNOTES/stnotes7.pdf

=> e aluminum gallium nitride/cn
E1 1 ALUMINUM GALLIUM NICKEL SILICON HYDROXIDE OXIDE/CN
E2 1 ALUMINUM GALLIUM NIOBIUM NITRIDE (AL0.1GA0.8*NB0.02N)/CN
E3 0 --> ALUMINUM GALLIUM NITRIDE/CN
E4 1 ALUMINUM GALLIUM NITRIDE (AL,GA N)/CN
E5 1 ALUMINUM GALLIUM NITRIDE (AL0-0.05GA0.95-1N) CN
E6 1 ALUMINUM GALLIUM NITRIDE (AL0-0.06GA0.94-1N) CN
E7 1 ALUMINUM GALLIUM NITRIDE (AL0-0.14GA0.86-1N) CN
E8 1 ALUMINUM GALLIUM NITRIDE (AL0-0.13GA0.87-1N) CN
E9 1 ALUMINUM GALLIUM NITRIDE (AL0-0.14GA0.86-1N) CN
E10 1 ALUMINUM GALLIUM NITRIDE (AL0-0.16GA0.84-1N) CN
E11 1 ALUMINUM GALLIUM NITRIDE (AL0-0.17GA0.83-1N) CN
E12 1 ALUMINUM GALLIUM NITRIDE (AL0-0.1GA0.9-1N)/CN

=> s e4
L1 1 "ALUMINUM GALLIUM NITRIDE ((AL,GA N)" CN

=> d l1

L1 ANSWER 1 OF 1 REGISTRY COPYRIGHT 2000 ACS
RN 176097-44-8 REGISTRY
CN **Aluminum gallium nitride ((Al,Ga)N) (9CI)** (CA INDEX NAME)
OTHER NAMES:
CN Aluminum gallium nitride (Al0-1Ga0-1N)
MF Al . Ga . N
AF Al0-1 Ga0-1 N
CI TIC
SR CA
LC STN Files: CA, CAPLUS, TOXCENTER, USPAT2, USPATFULL

Component	Ratio	Component Registry Number
N	1	17778-88-0
Ga	0 - 1	7440-55-3
Al	0 - 1	7429-90-5

2296 REFERENCES IN FILE CA (1967 TO DATE)
2 REFERENCES TO NON-SPECIFIC DERIVATIVES IN FILE CA
2313 REFERENCES IN FILE CAPLUS (1967 TO DATE)

=> file caplus
COST IN U.S. DOLLARS SINCE FILE ENTRY TOTAL SESSION

FULL ESTIMATED COST 9.38 9.59

FILE 'CAPLUS' ENTERED AT 09:39:37 ON 04 JUN 2002
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FILE COVERS 1907 - 4 Jun 2002 VOL 136 ISS 23
FILE LAST UPDATED: 2 Jun 2002 (20020602/ED)

This file contains CAS Registry Numbers for easy and accurate substance identification.

CAS roles have been modified effective December 16, 2001. Please check your SDI profiles to see if they need to be revised. For information on CAS roles, enter HELP ROLES at an arrow prompt or use the CAS Roles thesaurus (/RL field) in this file.

```
=> s l1
L2          3303 L1

=> s epitaxial growth
         69109 EPITAXIAL
               (EPITAXIAL OR EPITAXIALS)
         99168 GROWTH
               (GROWTH OR GROWTHS)
L3       19818 EPITAXIAL GROWTH
               (EPITAXIAL(W)GROWTH)

=> s l2 and l3
L4          66 L2 AND L3

=> d l4 1-66 ibib abs

L4   ANSWER 1 OF 66  CAPLUS  COPYRIGHT 2002 ACS
ACCESSION NUMBER:         2002:261146  CAPLUS
DOCUMENT NUMBER:          136:333314
TITLE:                    Gas source molecular beam epitaxy of high quality
                          AlGaN on Si and sapphire
AUTHOR(S):                Nikishin, S.; Kipshidze, G.; Kuryatkov, V.; Zubrilov,
                          A.; Choi, K.; Gherasoiu, I.; Grave de Peralta, L.;
                          Prokofyeva, T.; Holtz, M.; Asomoza, R.; Kudryavtsev,
                          Yu.; Temkin, H.
CORPORATE SOURCE:         Department of Electrical Engineering, Texas Tech
                          University, Lubbock, TX, 79401, USA
SOURCE:                   Materials Research Society Symposium Proceedings
                          (2001), 639(GaN and Related Alloys--2000),
                          G11.37/1-G11.37/6
                          CODEN: MRSPDH; ISSN: 0272-9172
PUBLISHER:                Materials Research Society
DOCUMENT TYPE:            Journal
LANGUAGE:                 English
AB   We report the results of epitaxial growth expts. on
```

AlxGa1-xN (0.ltoreq. x .ltoreq. 1) on Si(111) and sapphire substrates aimed at understanding the origin and elimination of cracking. We describe growth procedures resulting in thick layers of AlxGa1-xN, grown by gas source mol. beam epitaxy with ammonia, that are free of cracks. In GaN layers with the thickness of .apprx.2.5 .mu.m, we find the background electron concn. of (1-2).times.1016 cm-3 and mobility of (800.+-.100) cm2/Vs. In AlxGa1-xN (0.1 < x < 0.6) with the film thickness of 0.5-0.7 .mu.m the electron concn. of (2-3).times.1016 cm-3 is obtained. Low background concns. in GaN allow for formation of p-n junctions by doping with Mg. Light emitting diodes with the peak emission at 380 nm have been demonstrated.

REFERENCE COUNT: 19 THERE ARE 19 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L4 ANSWER 2 OF 66 CAPLUS COPYRIGHT 2002 ACS
ACCESSION NUMBER: 2000:761119 CAPLUS
DOCUMENT NUMBER: 136:347961
TITLE: AC operation of GaN:Er thin film electroluminescent display devices
AUTHOR(S): Heikenfeld, J.; Steckl, A. J.
CORPORATE SOURCE: Nanoelectronics Laboratory, University of Cincinnati, Cincinnati, OH, 45221-0030, USA
SOURCE: Materials Research Society Symposium Proceedings (2000), 639(GaN and Related Alloys--2000), G10.47.1-G10.47.6
CODEN: MRSPDH; ISSN: 0272-9172
PUBLISHER: Materials Research Society
DOCUMENT TYPE: Journal
LANGUAGE: English

AB Thin-film electroluminescence was obtained from GaN:Er deposited directly on amorphous dielec. layers. Electroluminescent device (ELD) structures consisting of a dielec./GaN/dielec. were formed on p+-Si substrates. In contrast to previous GaN:Er ELDs which used **epitaxial growth** conditions on cryst. substrates and were operated under d.c. bias, these ELDs were operated under a.c. bias. A max. luminance value of 300, 60, and 15 cd/m2 was achieved from GaN:Er and AlGaN:Er AC-ELDs biased at 180 V and 100, 10, and 1 kHz, resp. The emission spectra, which originate from Er3+ 4f-4f transitions, consist of dominant visible emission at .apprx.537/558 nm and IR emission at 1.5 .mu.m. A violet emission peak at 415 nm indicates that hot carriers can gain up to .apprx.3 eV energy for an applied voltage corresponding to 1.5 MV/cm applied field. The emitted intensity initially increases linearly with frequency, followed by a trend towards satn. The frequency for 3 dB redn. from the linear relation is at .apprx.65 kHz for visible emission and .apprx.8 kHz for IR emission. The satn. trends can be explained in terms of the spontaneous emission lifetimes of the visible (.apprx.10 .mu.s) and IR (.apprx.1ms) Er3+ emissions.

REFERENCE COUNT: 17 THERE ARE 17 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

=> file reg
COST IN U.S. DOLLARS

	SINCE FILE ENTRY	TOTAL SESSION
FULL ESTIMATED COST	14.17	28.76

DISCOUNT AMOUNTS (FOR QUALIFYING ACCOUNTS)

	SINCE FILE ENTRY	TOTAL SESSION
CA SUBSCRIBER PRICE	-1.24	-1.24

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STRUCTURE FILE UPDATES: 2 JUN 2002 HIGHEST RN 424787-53-0
DICTIONARY FILE UPDATES: 3 JUN 2002 HIGHEST RN 424787-53-0

TSCA INFORMATION NOW CURRENT THROUGH January 7, 2002

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Crossover limits have been increased. See HELP CROSSOVER for details.

Calculated physical property data is now available. See HELP PROPERTIES for more information. See STNote 27, Searching Properties in the CAS Registry File, for complete details:
http://www.cas.org/ONLINE/STN/STNOTES/stnotes27.pdf

=> d his

(FILE 'HOME' ENTERED AT 08:32:04 ON 04 JUN 2002)

FILE 'REGISTRY' ENTERED AT 08:33:41 ON 04 JUN 2002
E ALUMINUM GALLIUM NITRIDE/CN
L1 1 S E4

FILE 'CAPLUS' ENTERED AT 08:39:37 ON 04 JUN 2002
L2 2313 S L1
L3 19818 S EPITAXIAL GROWTH
L4 66 S L2 AND L3

FILE 'REGISTRY' ENTERED AT 08:49:11 ON 04 JUN 2002

=> e aluminum gallium nitride/cn
E1 1 ALUMINUM GALLIUM NICKEL SILICON HYDROXIDE OXIDE/CN
E2 1 ALUMINUM GALLIUM NIOBIUM NITRIDE (AL0.1GA0.8NB0.02N)/CN
E3 0 --> ALUMINUM GALLIUM NITRIDE/CN
E4 1 ALUMINUM GALLIUM NITRIDE (AL,GA)N/CN
E5 1 ALUMINUM GALLIUM NITRIDE (AL0-0.05GA0.95-1N)/CN
E6 1 ALUMINUM GALLIUM NITRIDE (AL0-0.06GA0.94-1N)/CN
E7 1 ALUMINUM GALLIUM NITRIDE (AL0-0.12GA0.88-1N)/CN
E8 1 ALUMINUM GALLIUM NITRIDE (AL0-0.13GA0.87-1N)/CN
E9 1 ALUMINUM GALLIUM NITRIDE (AL0-0.14GA0.86-1N)/CN
E10 1 ALUMINUM GALLIUM NITRIDE (AL0-0.16GA0.84-1N)/CN
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E12 1 ALUMINUM GALLIUM NITRIDE (AL0-0.18GA0.9-1N)/CN

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=
E133            1    ALUMINUM GALLIUM NITRIDE (AL0.7-1GA0-0.3N)/CN
E134            1    ALUMINUM GALLIUM NITRIDE (AL0.71GA0.29N)/CN
E135            1    ALUMINUM GALLIUM NITRIDE (AL0.72GA0.28N)/CN
E136            1    ALUMINUM GALLIUM NITRIDE (AL0.73GA0.27N)/CN
E137            1    ALUMINUM GALLIUM NITRIDE (AL0.74GA0.26N)/CN
E138            1    ALUMINUM GALLIUM NITRIDE (AL0.76GA0.24N)/CN
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E139 1 ALUMINUM GALLIUM NITRIDE (AL0.77GA0.23N)/CN
E140 1 ALUMINUM GALLIUM NITRIDE (AL0.76GA0.24N)/CN
E141 1 ALUMINUM GALLIUM NITRIDE (AL0.79GA0.21N)/CN
E142 1 ALUMINUM GALLIUM NITRIDE (AL0.7GA0.3N)/CN
E143 1 ALUMINUM GALLIUM NITRIDE (AL0.9-1.0GA0.1-0.2N)/CN
E144 1 ALUMINUM GALLIUM NITRIDE (AL0.81GA0.19N)/CN

=> s
E145 1 ALUMINUM GALLIUM NITRIDE (AL0.82GA0.18N)/CN
E146 1 ALUMINUM GALLIUM NITRIDE (AL0.84GA0.16N)/CN
E147 1 ALUMINUM GALLIUM NITRIDE (AL0.85-0.95GA0.05-0.15N)/CN
E148 1 ALUMINUM GALLIUM NITRIDE (AL0.85-0.9GA0.1-0.15N)/CN
E149 1 ALUMINUM GALLIUM NITRIDE (AL0.85GA0.15N)/CN
E150 1 ALUMINUM GALLIUM NITRIDE (AL0.86GA0.14N)/CN
E151 1 ALUMINUM GALLIUM NITRIDE (AL0.87GA0.13N)/CN
E152 1 ALUMINUM GALLIUM NITRIDE (AL0.88GA0.12N)/CN
E153 1 ALUMINUM GALLIUM NITRIDE (AL0.89GA0.11N)/CN
E154 1 ALUMINUM GALLIUM NITRIDE (AL0.9GA0.1N)/CN
E155 1 ALUMINUM GALLIUM NITRIDE (AL0.93GA0.07N)/CN
E156 1 ALUMINUM GALLIUM NITRIDE (AL0.94GA0.06N)/CN

=> s
E157 1 ALUMINUM GALLIUM NITRIDE (AL0.95GA0.05N)/CN
E158 1 ALUMINUM GALLIUM NITRIDE (AL0.96GA0.04N)/CN
E159 1 ALUMINUM GALLIUM NITRIDE (AL0.97GA0.03N)/CN
E160 1 ALUMINUM GALLIUM NITRIDE (AL0.98GA0.02N)/CN
E161 1 ALUMINUM GALLIUM NITRIDE (AL0.9GA0.1N)/CN
E162 1 ALUMINUM GALLIUM NITRIDE (AL3GAN4)/CN
E163 1 ALUMINUM GALLIUM NITRIDE (AL3GA1N4)/CN
E164 1 ALUMINUM GALLIUM NITRIDE (AL3GAN2)/CN
E165 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE/CN
E166 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE ((AL,GA)(N,P))/CN
E167 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE ((AL,GA)N).8-1P0-0.2)/CN
E168 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.70GA0.30N0.92P0.08)/
CN

=> s
E169 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.70GA0.30N0.98P0.02)/
CN
E170 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.83GA0.17N0.88P0.12)/
CN
E171 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.90GA0.10N0.98P0.02)/
CN
E172 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.95GA0.05N0.95P0.05)/
CN
E173 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.95GA0.05N0.99P0.01)/
CN
E174 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.95GA0.05N0.95P0.05)/
CN
E175 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.95GA0.05N0.94P0.06)/CN
E176 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.95GA0.05N0.99P0.01)/CN
E177 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.95GA0.05N0.96P0.04)/CN
E178 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.95GA0.05N0.99P0.1)/CN
E179 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.90GA0.10N0.98P0.02)/CN
E180 1 ALUMINUM GALLIUM NITRIDE PHOSPHIDE (AL0.90GA0.10N0.95P0.05)/CN

=> s e1-164
L5 161 ("ALUMINUM GALLIUM NICKEL SILICON HYDROXIDE OXIDE"/CN OR "ALUMIN
UM GALLIUM NIOBIUM NITRIDE (AL0.1GA0.8)NB0.1)N "/CN OR "ALUMINUM
GALLIUM NITRIDE"/CN OR "ALUMINUM GALLIUM NITRIDE (AL,GA)N)"/CN
OR "ALUMINUM GALLIUM NITRIDE (AL0-0.05GA0.95-1N)"/CN OR "ALUMIN
UM GALLIUM NITRIDE (AL0-0.06GA0.94-1N)"/CN OR "ALUMINUM GALLIUM
NITRIDE (AL0-0.12GA0.88-1N)"/CN OR "ALUMINUM GALLIUM NITRIDE
(AL0-0.13GA0.87-1N)"/CN OR "ALUMINUM GALLIUM NITRIDE (AL0-0.14GA

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.36-1N)"/CN OR "ALUMINUM GALLIUM NITRIDE (ALO-0.16GA0.84-1N)"/C
N OF "ALUMINUM GALLIUM NITRIDE (ALO-0.1?GA0.8?-1N)"/CN OR "ALUMI
NUM GALLIUM NITRIDE (ALO-0.1GA0.9-1N)"/CN OR "ALUMINUM GALLIUM
NITRIDE (ALO-0.2GA0.?8-1N)"/CN OR "ALUMINUM GALLIUM NITRIDE
(ALO-0.25GA0.75-1N,"/CN OR "ALUMINUM GALLIUM NITRIDE (ALO-0.2GA0
.8-1N)"/CN OR "ALUMINUM GALLIUM NITRIDE (ALO-0.3?GA0.65-1N)"/CN
OR "ALUMINUM GALLIUM NITRIDE (ALO-0.3GA0.7-1N,"/CN OR "ALUMINUM
GALLIUM NITRIDE (ALO-0.45GA0.55-1N)"/CN OR "ALUMINUM GALLIUM
NITRIDE (ALO-0.4GA0.6-1N)"/CN OR "ALUMI

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                                                      ENTRY     SESSION
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=> d his

     (FILE 'HOME' ENTERED AT 08:34:04 ON 04 JUN 2002)

     FILE 'REGISTRY' ENTERED AT 08:35:41 ON 04 JUN 2002
                E ALUMINUM GALLIUM NITRIDE/CN
L1             1 S E4

     FILE 'CAPLUS' ENTERED AT 08:39:37 ON 04 JUN 2002
L2          2976 S L1
L3         19614 S EPITAXIAL GROWTH
L4            56 S L2 AND L3

     FILE 'REGISTRY' ENTERED AT 08:49:11 ON 04 JUN 2002
                E ALUMINUM GALLIUM NITRIDE/CN
L5           161 S E1-164

     FILE 'CAPLUS' ENTERED AT 13:13:54 ON 04 JUN 2002
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=> s l5
L6 4473 L5

=> s l6 and l3
L7 193 L6 AND L3

=> d scan

L7 193 ANSWERS CAPLUS COPYRIGHT 2002 ACS
CC 76-3 (Electric Phenomena)
Section cross-reference(s): 75
TI Growth of gallium nitride and aluminum gallium nitride thin films using conventional and pendeo-**epitaxial growth** processes on 6H-silicon carbide(0001) and silicon(111) substrates
ST aluminum gallium nitride heterostructure silicon carbide
IT Heterojunction semiconductor devices
(growth of GaN and (Al,Ga)N thin films using conventional and pendeo-**epitaxial growth** processes on (0001)6H-SiC and (111) Si substrates for)
IT 409-21-2, Silicon monocarbide, processes 25617-97-4, Gallium nitride (GaN) **106097-44-3**, Aluminum gallium nitride Al0-1ga0-1n
RL: PEP (Physical, engineering or chemical process); PYP (Physical process); TEM (Technical or engineered material use); PROC (Process); USES (Uses)
(growth of GaN and (Al,Ga)N thin films using conventional and pendeo-**epitaxial growth** processes on (0001)6H-SiC and (111)Si substrates)

HOW MANY MORE ANSWERS DO YOU WISH TO SCAN? (1):1

L7 193 ANSWERS CAPLUS COPYRIGHT 2002 ACS
IC ICM H01L029-36
ICS H01L021-0338; H01L031-0336; H01L031-072; H01L031-109; H01L021-3205; H01L021-4763
NCL 257/194000
CC 76-3 (Electric Phenomena)
TI Design and fabrication of a GaN field-effect transistor and an inverter device
ST semiconductor device fabrication gallium nitride field effect transistor inverter
IT Doping
Electron acceptors
Electron donors
Epitaxy
Field effect transistors
Inverters
Ion implantation
MISFET (transistors)
Semiconductor device fabrication
Semiconductor heterojunctions
(design and fabrication of a GaN field-effect transistor and inverter device)
IT 249-14-0, Aluminum nitride 25617-97-4, Gallium nitride (GaN) **106097-44-3**, Aluminum gallium nitride ((Al,Ga)N)
RL: DEV (Device component use); TEM (Technical or engineered material use); USES (Uses)
(design and fabrication of a GaN field-effect transistor and inverter device)
IT 7439-95-4, Magnesium, uses 7440-44-0, Carbon, uses 7440-66-6, Zinc, uses
RL: MOA (Modifier or additive use); USES (Uses)
(design and fabrication of a GaN field-effect transistor and inverter device)

HOW MANY MORE ANSWERS DO YOU WISH TO SCAN? (1):0

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MISSING OPERATOR L7 5-12
The search profile that was entered contains terms or
nested terms that are not separated by a logical operator.

=> s l7 py >= 2001 abs ibib
MISSING OPERATOR L7 5Y
The search profile that was entered contains terms or
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=> s l7 py > 2001
MISSING OPERATOR L7 5Y
The search profile that was entered contains terms or
nested terms that are not separated by a logical operator.

=> s l7 py > 2001
    103 ANSWERS ARE AVAILABLE. SPECIFIED ANSWER NUMBER EXCEEDS ANSWER SET SIZE
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NUMBERS IN RANGE MUST BE GREATER THAN ZERO.
An answer number must be a positive number.
ENTER ANSWER NUMBER OR RANGE (1):1
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DALL -------- ALL, delimited (end of each field identified)
DMAX -------- MAX, delimited for post-processing
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FBIB -------- AN, BIB, plus Patent FAM
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              e.g., D SCAN or DISPLAY SCAN)
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IALL -------- ALL, indented with text labels
IBIB -------- BIB, indented with text labels
IMAX -------- MAX, indented with text labels
ISTD -------- STD, indented with text labels

CBIB -------- AN, plus Bibliographic Data (original)
CIBIB ------- CBIB, indented with text labels

SBIB -------- BIB, no citations
SIBIB ------- IBIB, no citations

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              containing hit terms

HITRN ------- HIT RN and its text modification
HITSTR ------ HIT RN, its text modification, its CA index name, and its structure diagram
HITSEQ ------ HIT RN, its text modification, its CA index name, its structure diagram, plus NTE and SEQ fields
FHITSTR ----- First HIT RN, its text modification, its CA index name, and its structure diagram
FHITSEQ ----- First HIT RN, its text modification, its CA index name, its structure diagram, plus NTE and SEQ fields
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L7 ANSWER 1 OF 103 CAPLUS COPYRIGHT 2002 ACS
AN 2002:261146 CAPLUS
DN 136:333314
TI Gas source molecular beam epitaxy of high quality AlGaN on Si and sapphire
AU Nikishin, S.; Kipshidze, G.; Kuryatkov, V.; Zubrilov, A.; Choi, K.; Gherasoiu, Iu.; Grave de Peralta, L.; Prokofyeva, T.; Holtz, M.; Asomoza, R.; Kudryavtsev, Yu.; Temkin, H.
CS Department of Electrical Engineering, Texas Tech University, Lubbock, TX, 79401, USA
SO Materials Research Society Symposium Proceedings (2001), 639(GaN and Related Alloys--2000), G11.37/1-G11.37/6
    CODEN: MRSPDH; ISSN: 0272-9172
PB Materials Research Society
DT Journal
LA English
RE.CNT 29 THERE ARE 29 CITED REFERENCES AVAILABLE FOR THIS RECORD
            ALL CITATIONS AVAILABLE IN THE RE FORMAT

=> s l7 py < 2001
MISSING OPERATOR L7 PY
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=> s l7 and py < 2001
L8   86 L7 AND PY < 2001

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LOGOFF? (Y)/N/HOLD:n

=>